

PSMN7R0-100ES

N-channel 100V 6.8 $\mbox{m}\Omega$ standard level MOSFET in I2PAK.

Rev. 03 — 23 February 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in I2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	100	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	269	W
T_j	junction temperature			-55	-	175	°C
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} ≤ 100 V; unclamped; R_{GS} = 50 Ω		-	-	315	mJ
Dynamic	characteristics						
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 50 V; see <u>Figure 15</u> and <u>14</u>		-	36	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 50 V; see <u>Figure 14</u> and <u>15</u>		-	125	-	nC



Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$	-	-	12	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$	-	5.4	6.8	mΩ

^[1] Continuous current is limited by package

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		$G \longrightarrow X$
mb	D	mounting base; connected to drain		mbb076 S
			SOT226 (I2PAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN7R0-100ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

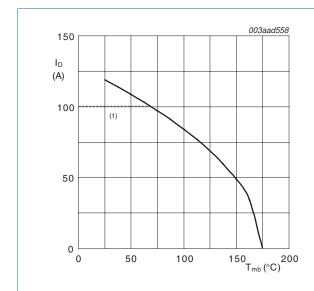
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	100	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>		-	85	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	Α
I _{DM}	peak drain current	$t_p \le 10 \mu\text{s}; \text{ pulsed}; T_{mb} = 25 ^{\circ}\text{C}; \text{ see } \underline{\text{Figure 3}}$		-	475	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	269	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-dr	ain diode					
Is	source current	T _{mb} = 25 °C;	<u>[1]</u>	-	100	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	475	Α
Avalanche	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 100 V; unclamped; R_{GS} = 50 Ω		-	315	mJ

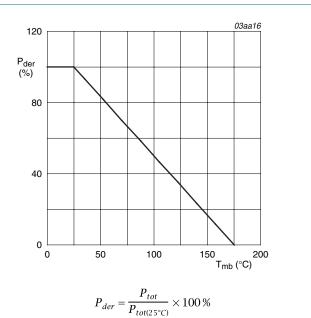
[1] Continuous current is limited by package



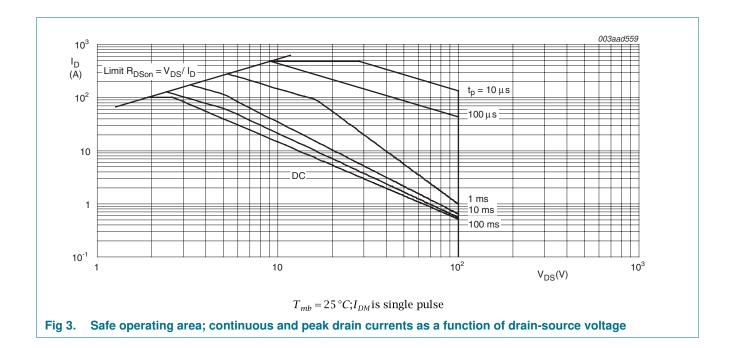
 $V_{GS} \ge 10 \text{ V}$; (1) capped at 100 A due to package.

mounting base temperature

Continuous drain current as a function of



ig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.3	0.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

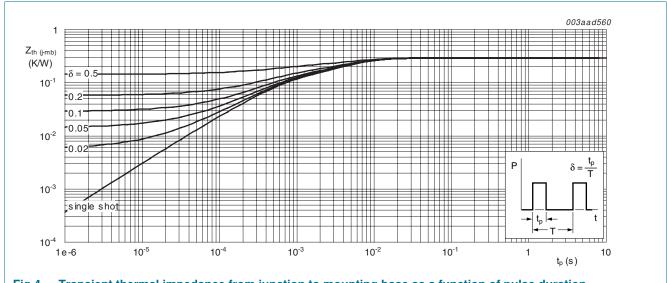


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
-	racteristics	Conditions	IVIIII	iyp	IVIAX	Unit
	drain-source	I _D = 0.25 mA; V _{GS} = 0 V; T _i = -55 °C	90	_	-	V
V _{(BR)DSS}	breakdown voltage	$I_D = 0.25 \text{ mA}, V_{GS} = 0 \text{ V}, T_j = 25 \text{ °C}$ $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C}$	100			V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_i = 175 \text{ °C}$; see Figure 10	1	_	_	V
▼GS(th)	voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 11 and 10	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_i = -55$ °C; see Figure 10	-	-	4.8	V
l _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 125 °C	-	-	150	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.08	4	μΑ
lgss	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	12	mΩ
	resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; see <u>Figure 12</u>	-	15	19	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$	-	5.4	6.8	mΩ
R_{G}	internal gate resistance (AC)	f = 1 MHz	-	0.74	-	Ω
Dynamic o	characteristics					
Q _{G(tot)} total gate charge	I_D = 25 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 14</u> and <u>15</u>	-	125	-	nC	
		$I_D = 0 A$; $V_{DS} = 0 V$; $V_{GS} = 10 V$	-	100	-	nC
Q_{GS}	gate-source charge	I_D = 25 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 15</u> and <u>14</u>	-	28	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 25 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 15</u>	-	19.4	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	9	-	nC
Q_GD	gate-drain charge	I_D = 25 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 15</u> and <u>14</u>	-	36	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 50 \text{ V}$; see <u>Figure 15</u> and <u>14</u>	-	4.3	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 °C;$	-	6686	-	pF
Coss	output capacitance	see Figure 16	-	438	-	pF
C _{rss}	reverse transfer capacitance		-	272	-	pF
·d(on)	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \Omega; V_{GS} = 10 \text{ V};$	-	34.6	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 °C$	-	45.6	-	ns
t _{d(off)}	turn-off delay time		-	103.9	-	ns
t _f	fall time		-	49.5	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	64	-	ns
Q _r	recovered charge	$V_{DS} = 50 \text{ V}$	-	167	-	nC

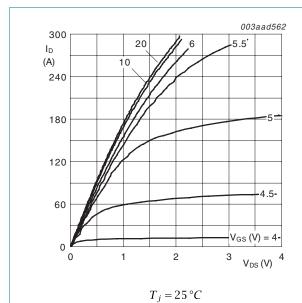


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

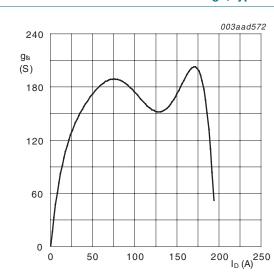


Fig 7. Forward transconductance as a function of drain current; typical values

 $T_j = 25 \,^{\circ}C; V_{DS} = 15 V$

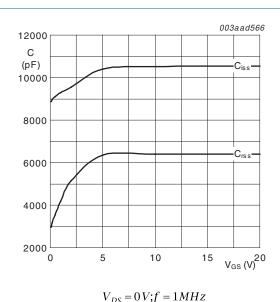


Fig 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

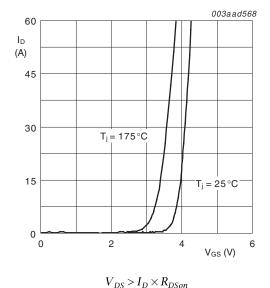


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

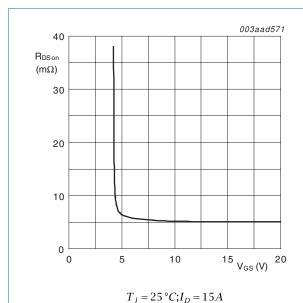


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

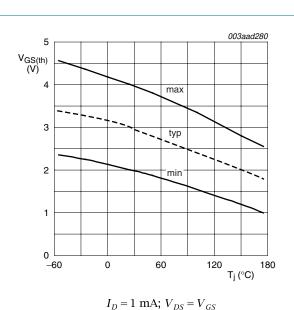


Fig 10. Gate-source threshold voltage as a function of junction temperature

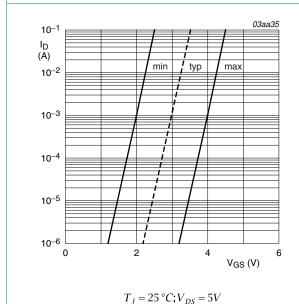


Fig 11. Sub-threshold drain current as a function of gate-source voltage

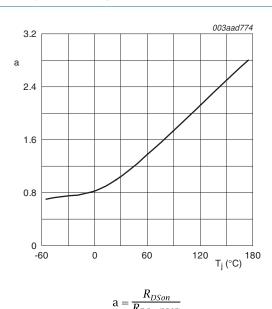


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

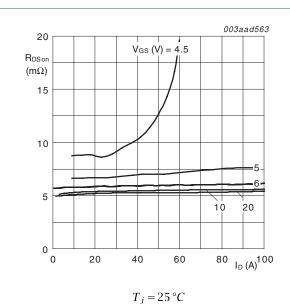
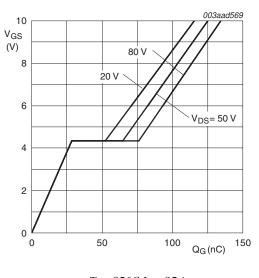


Fig 13. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25 \,^{\circ}C; I_D = 25A$

Fig 14. Gate-source voltage as a function of gate charge; typical values

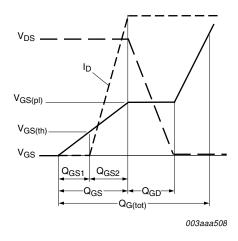
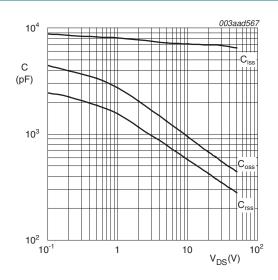
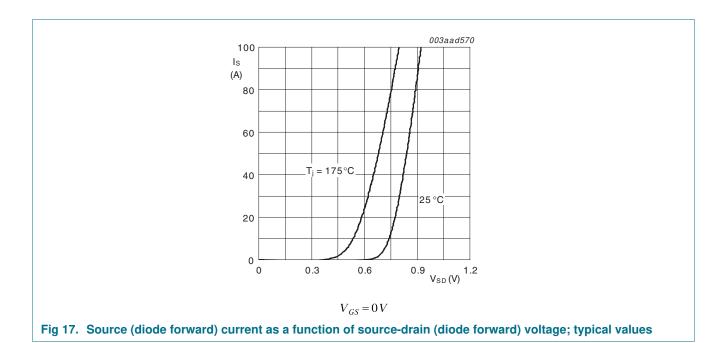


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



7. Package outline

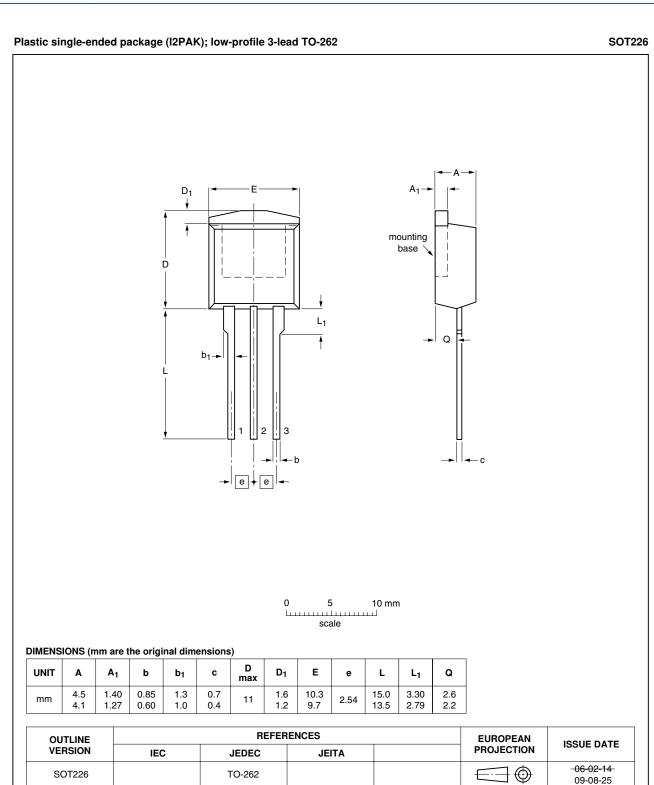


Fig 18. Package outline SOT226 (I2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R0-100ES_3	20100223	Product data sheet	-	PSMN7R0-100ES_2
Modifications:	 Various cha 	anges to content.		
PSMN7R0-100ES_2	20100114	Objective data sheet	-	PSMN7R0-100ES_1
PSMN7R0-100ES_1	20090917	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PSMN7R0-100ES_3

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PSMN7R0-100ES

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